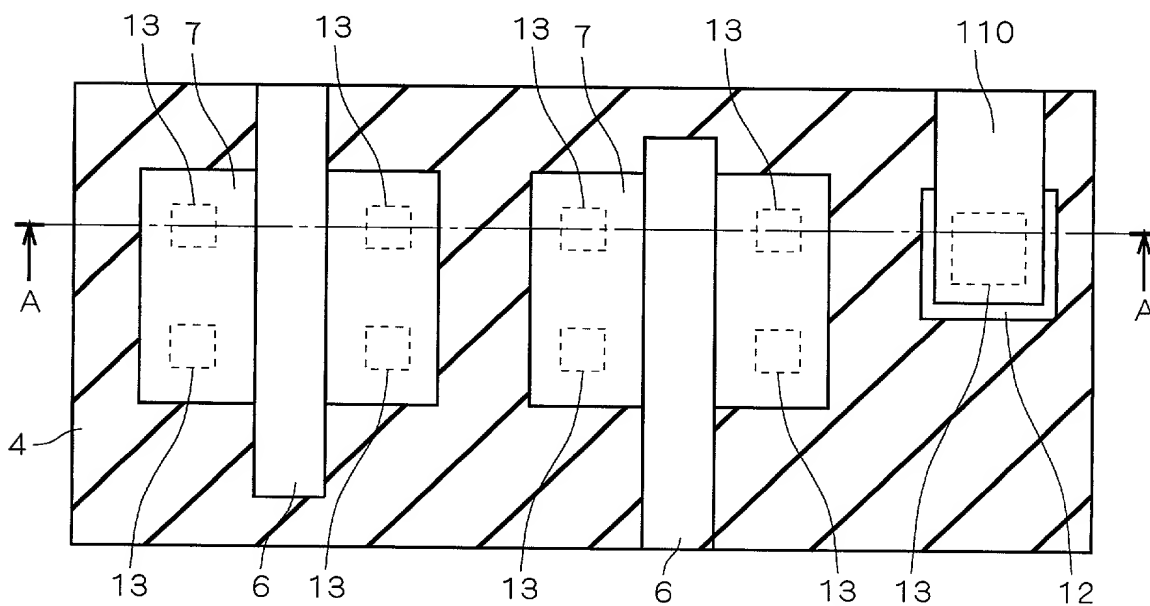


F I G . 2



F I G . 3

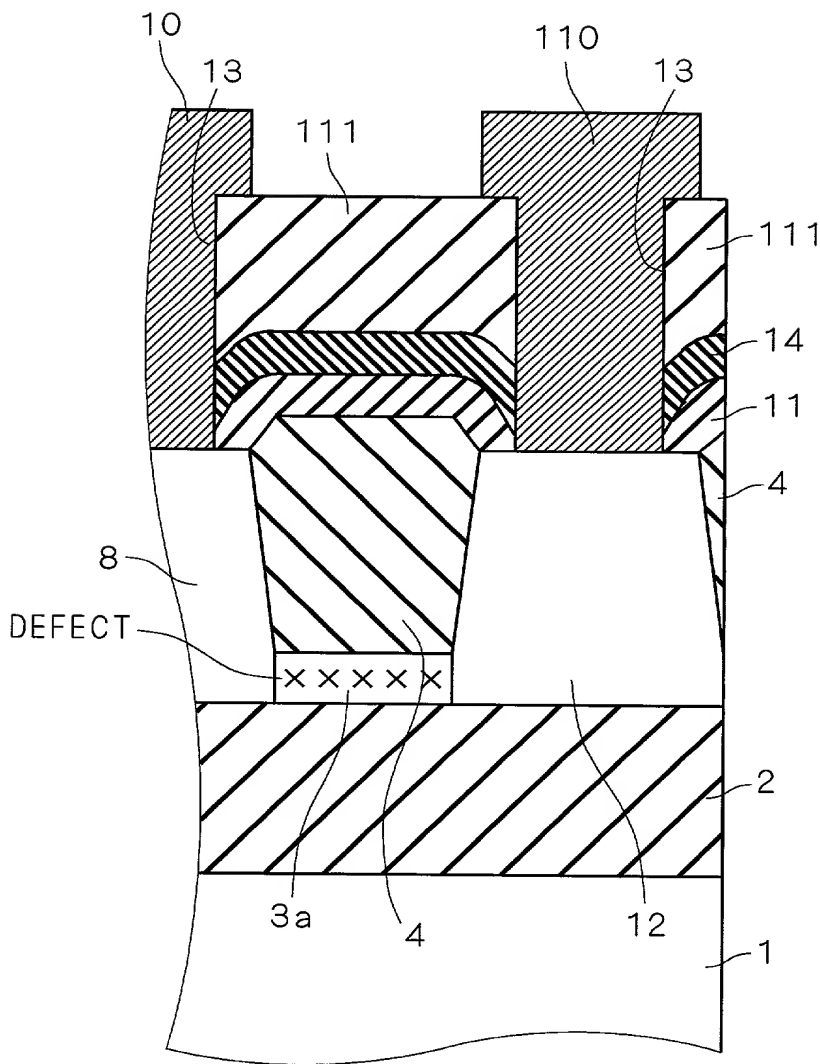


FIG. 4

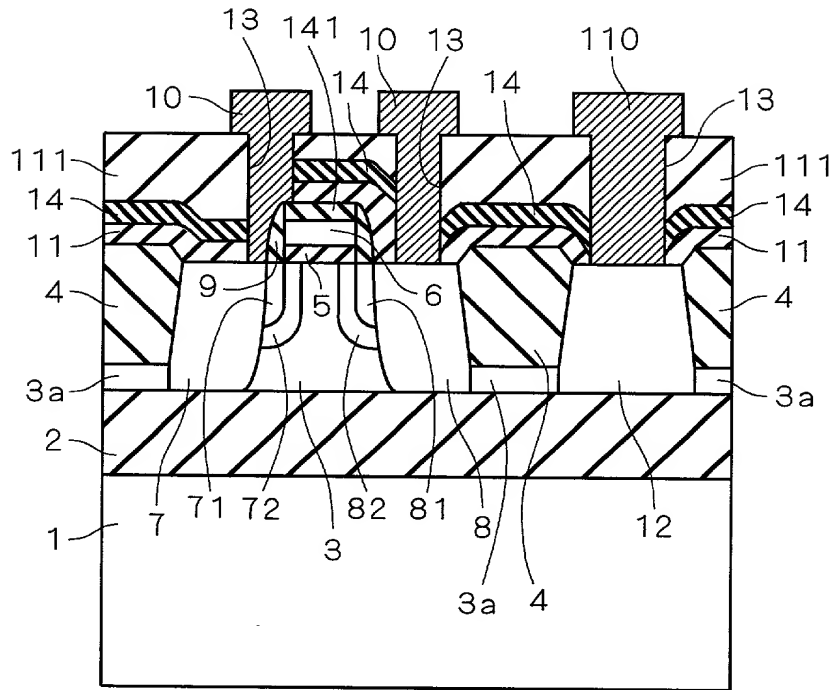


FIG. 5

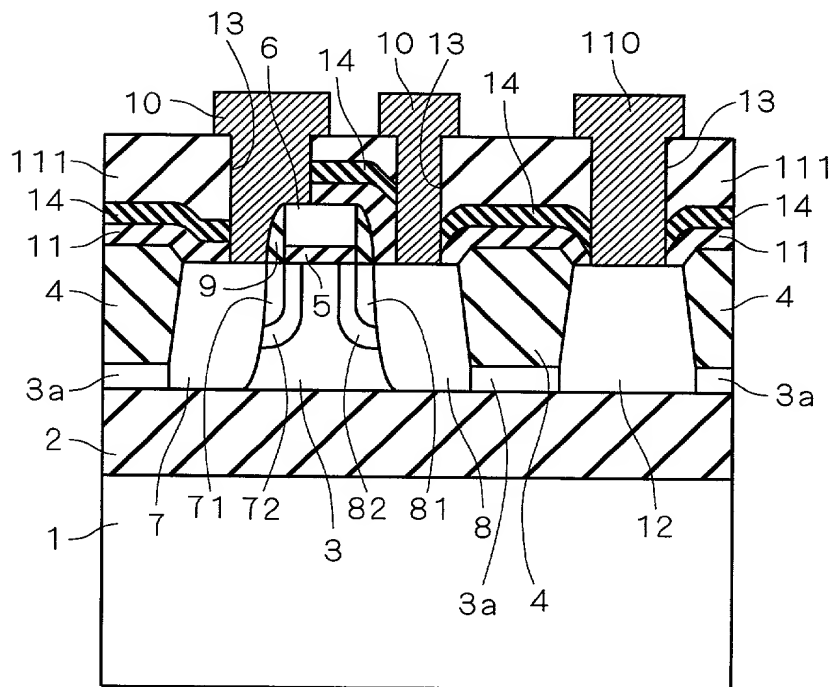


FIG. 6

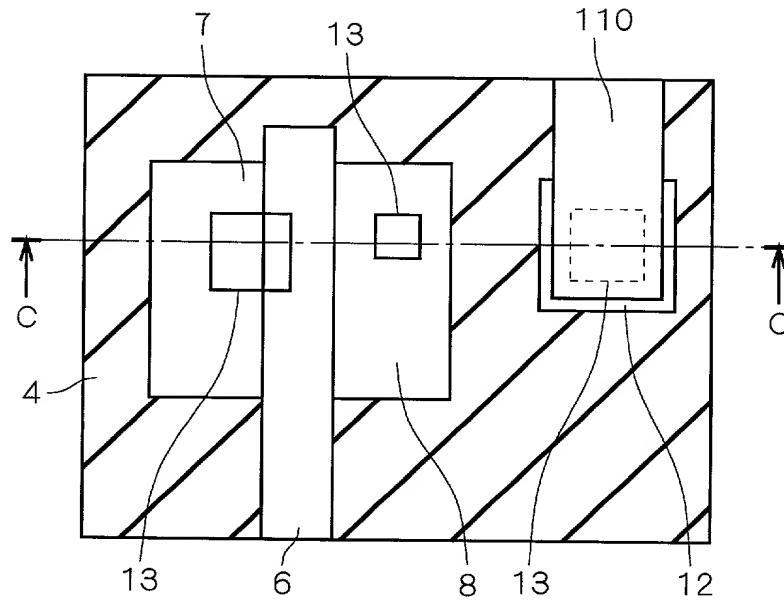


FIG. 7

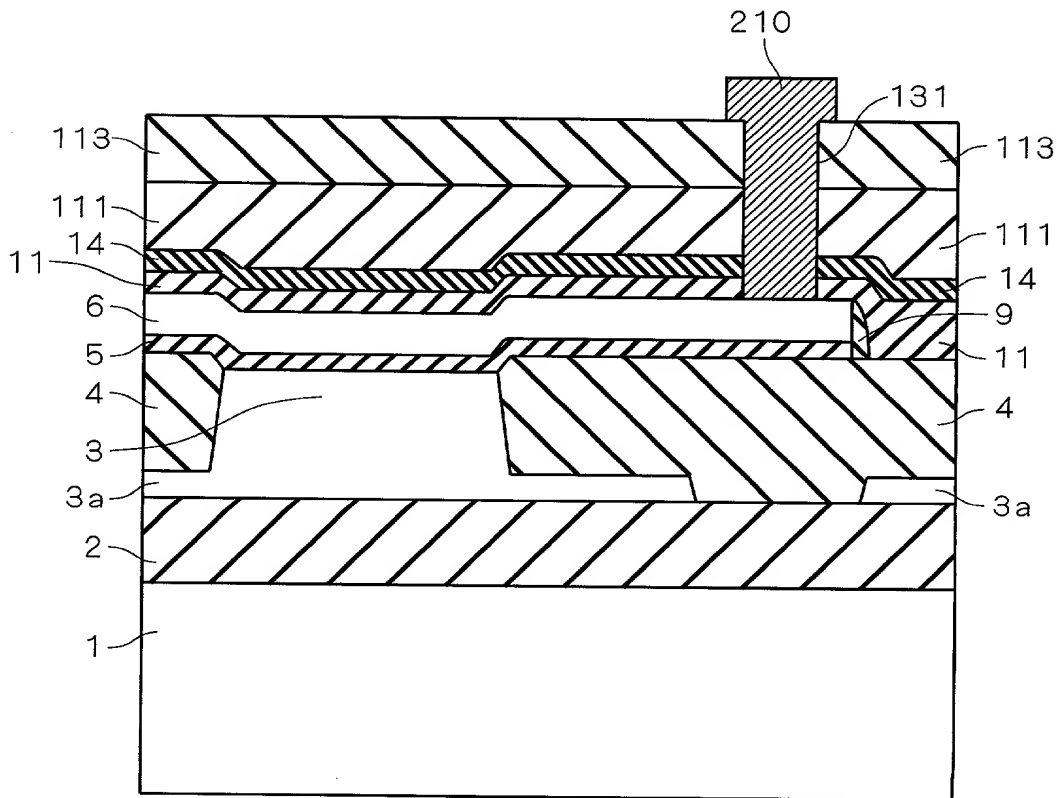


FIG. 8

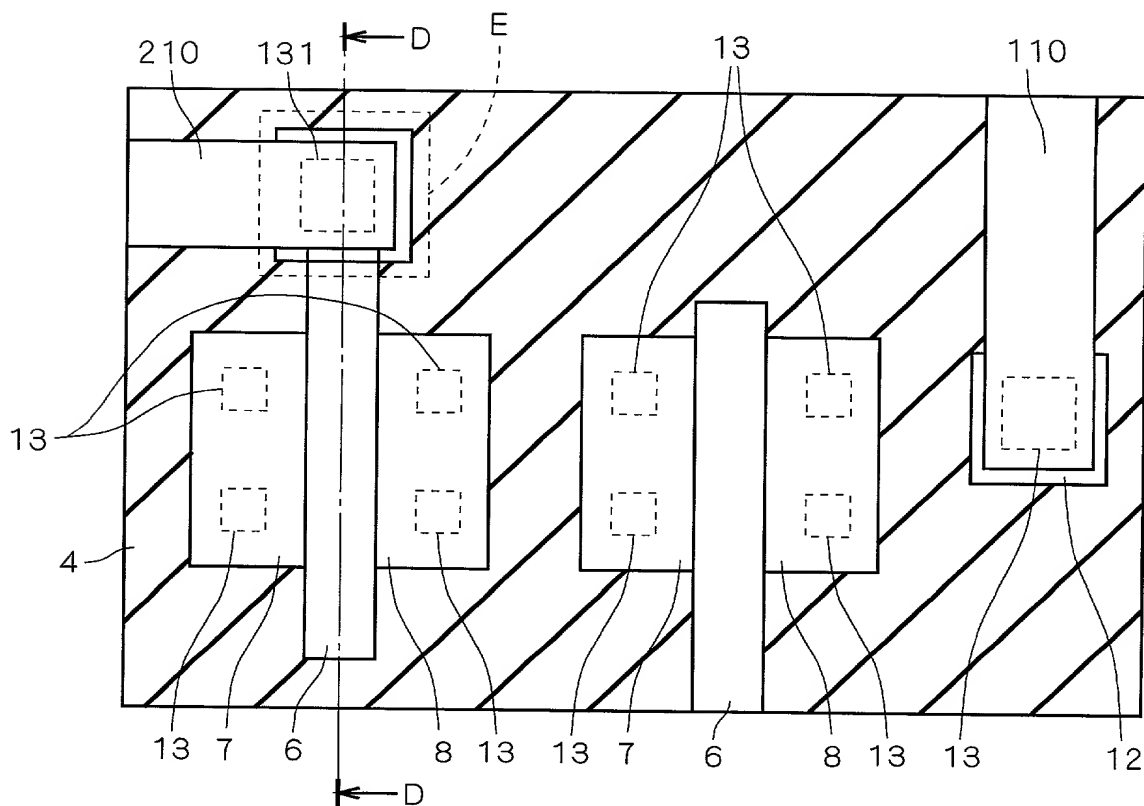


FIG. 9

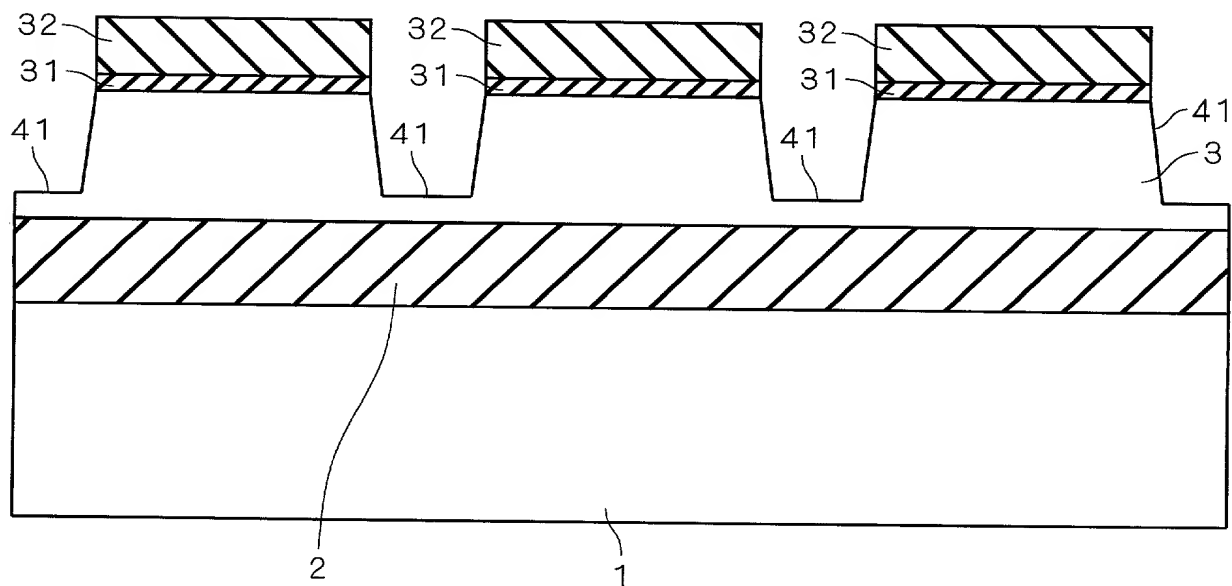


FIG. 10

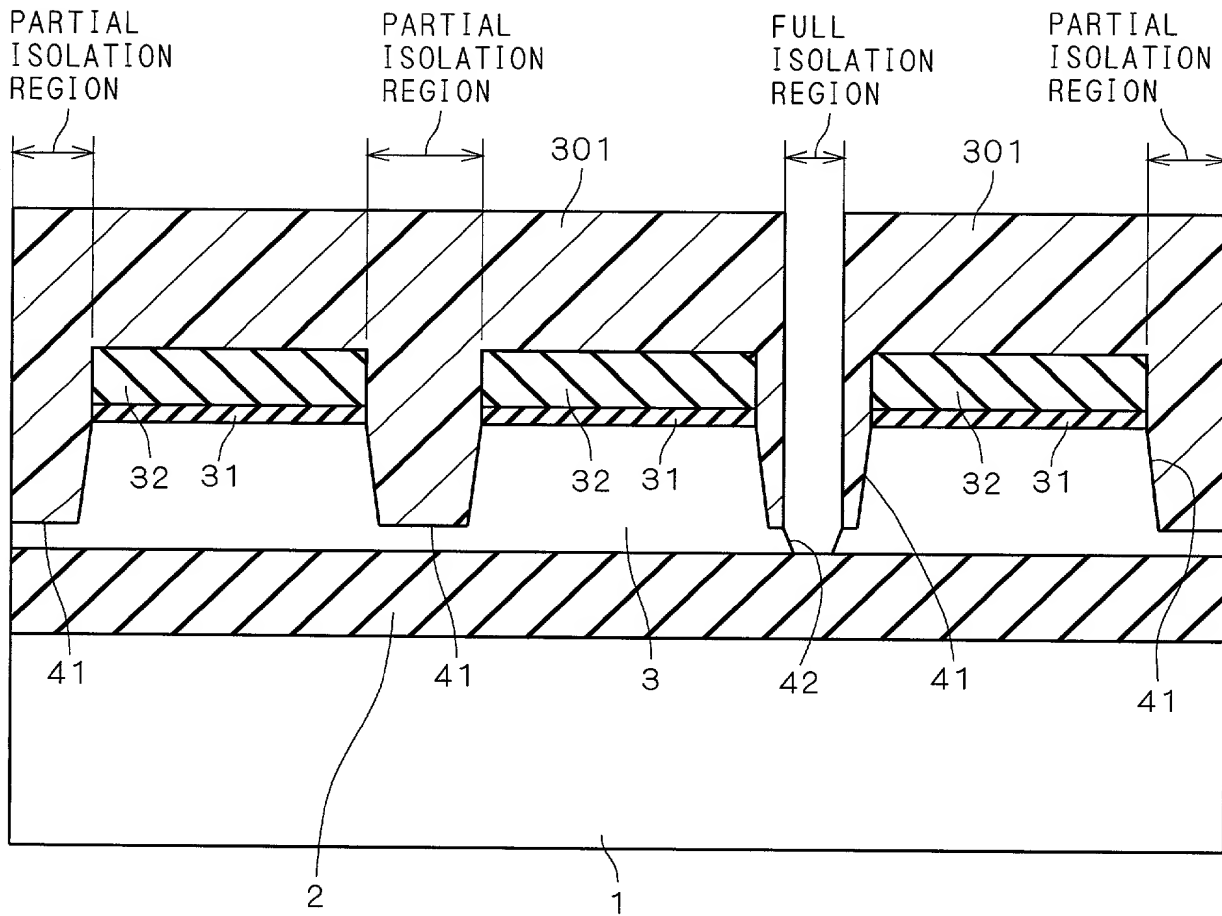


FIG. 11

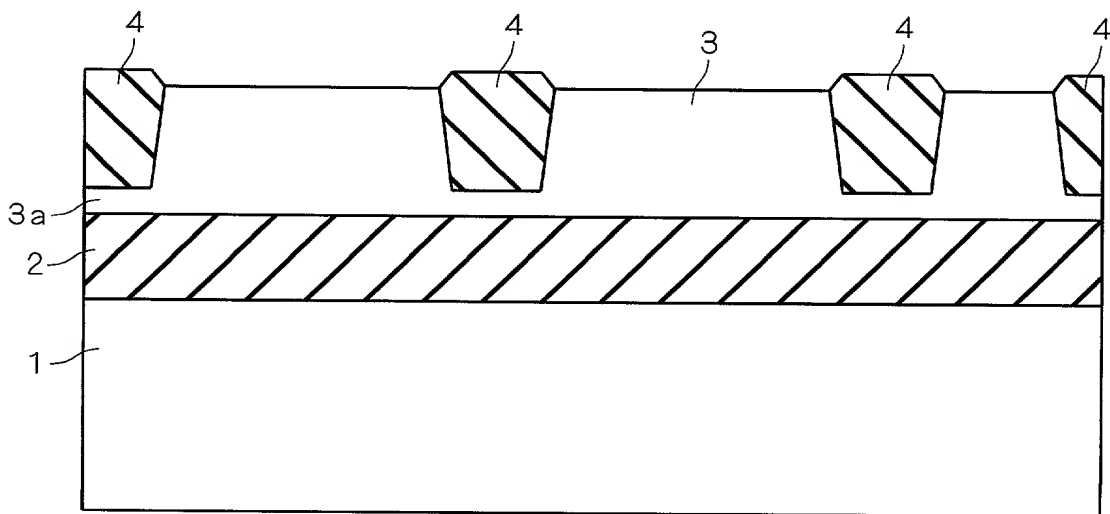


FIG. 12

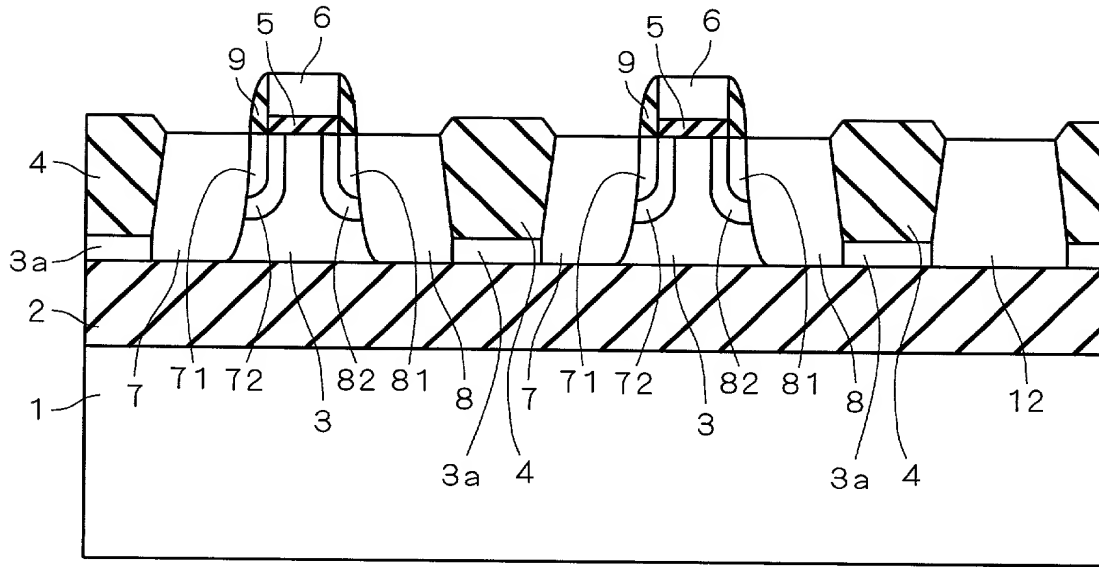
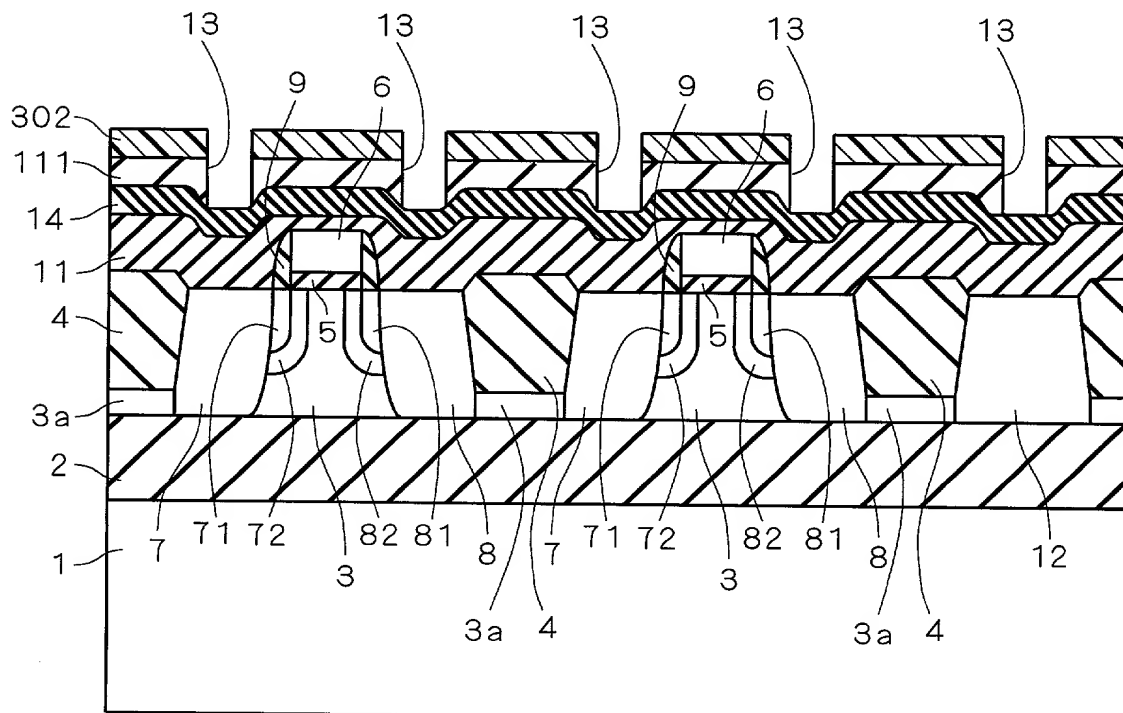


FIG. 13



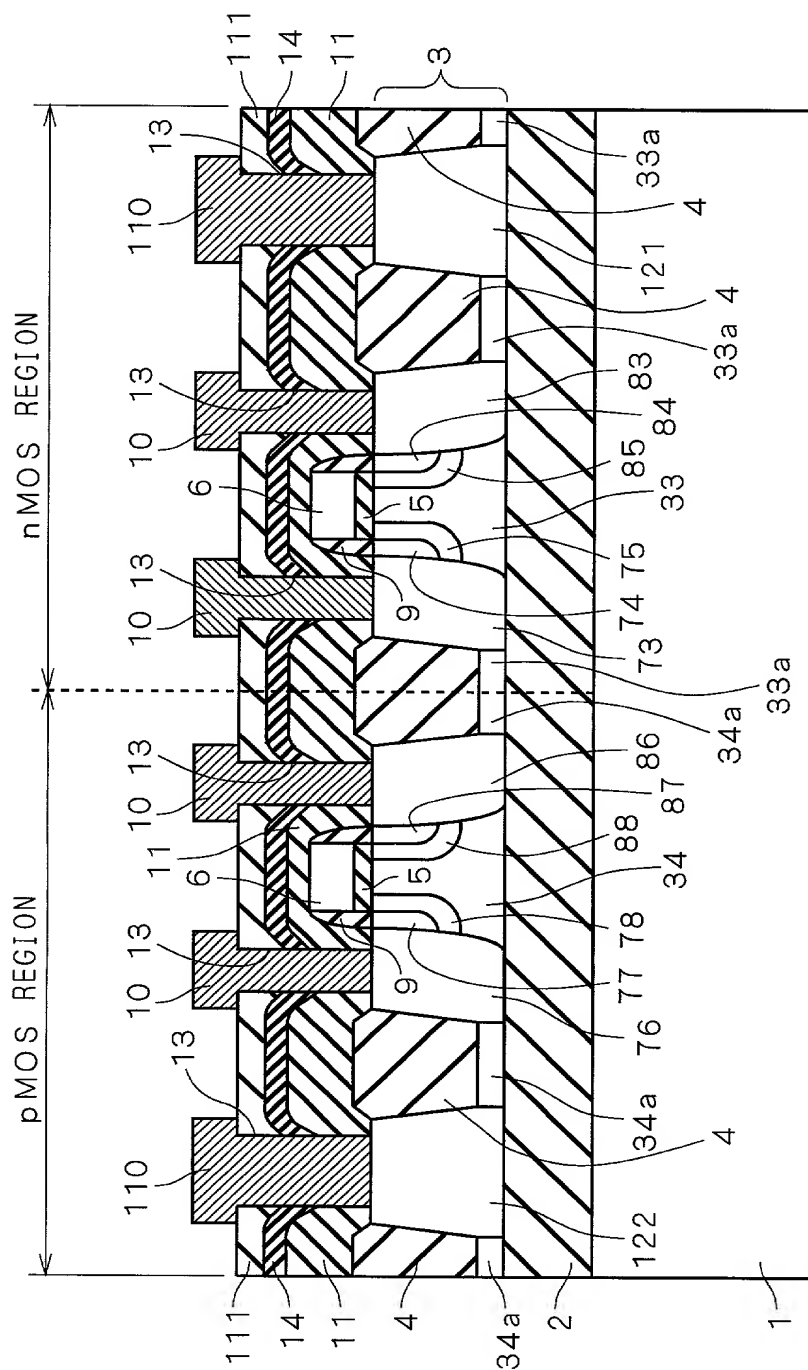


FIG. 14



FIG. 15

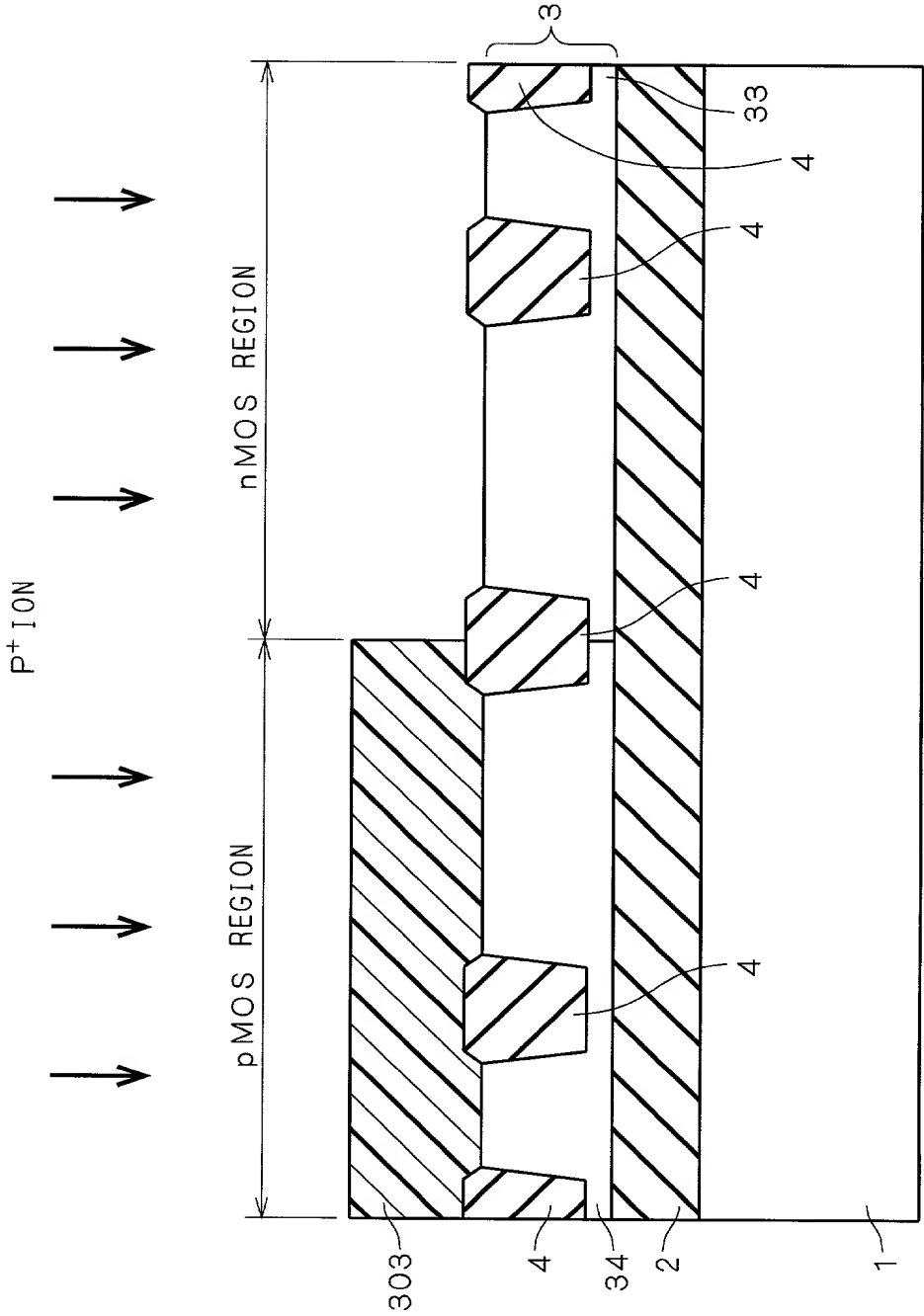


FIG. 16

A detailed cross-sectional diagram of a semiconductor device. The base layer is labeled 1. Above it are several layers: 2, 3, 4, 11, 14, and 111. A central structure consists of a pedestal 9 topped with a cap 6. To the left and right of this center are other features labeled 7, 8, 12, and 13. Various interfaces and regions are indicated by numbers like 310, 132, 110, 123, 3a, 71, 72, 81, 82, 4, and 5. Dashed vertical lines indicate specific boundaries or planes within the structure.

FIG. 21

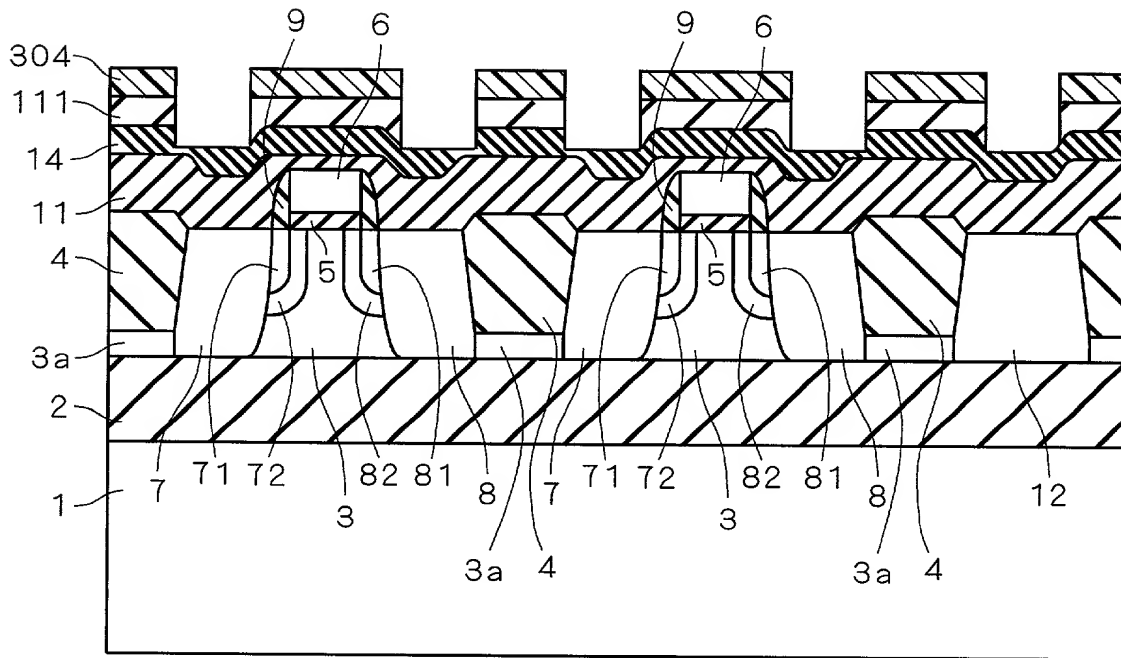


FIG. 22

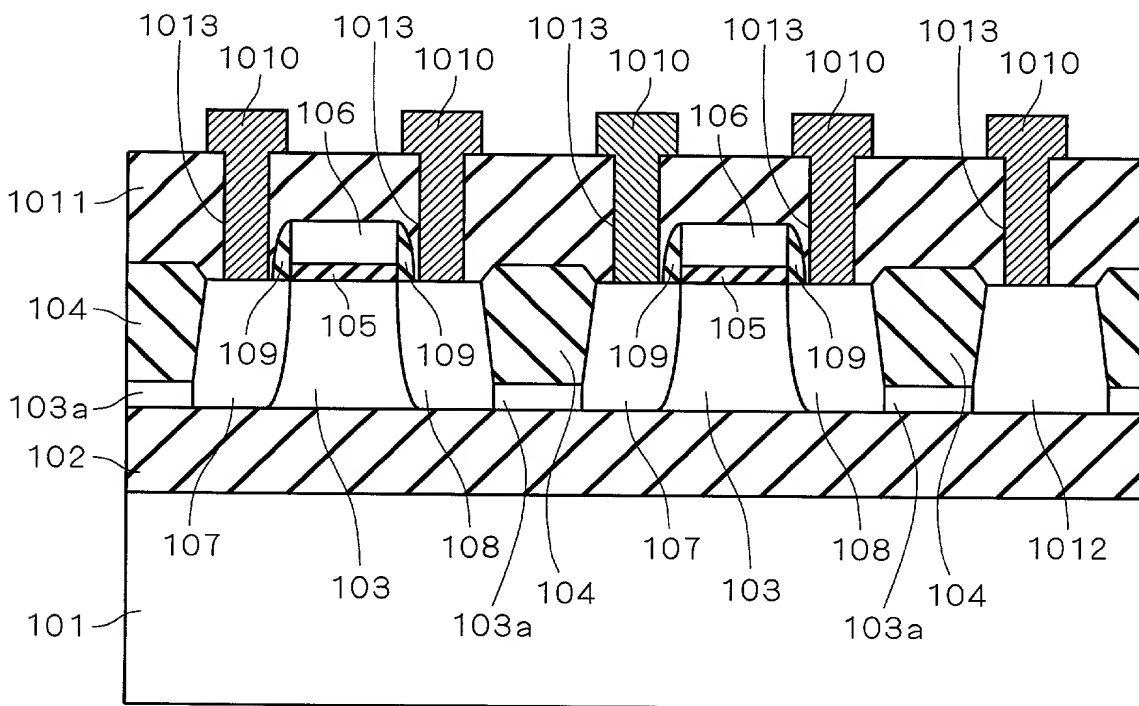


FIG. 23

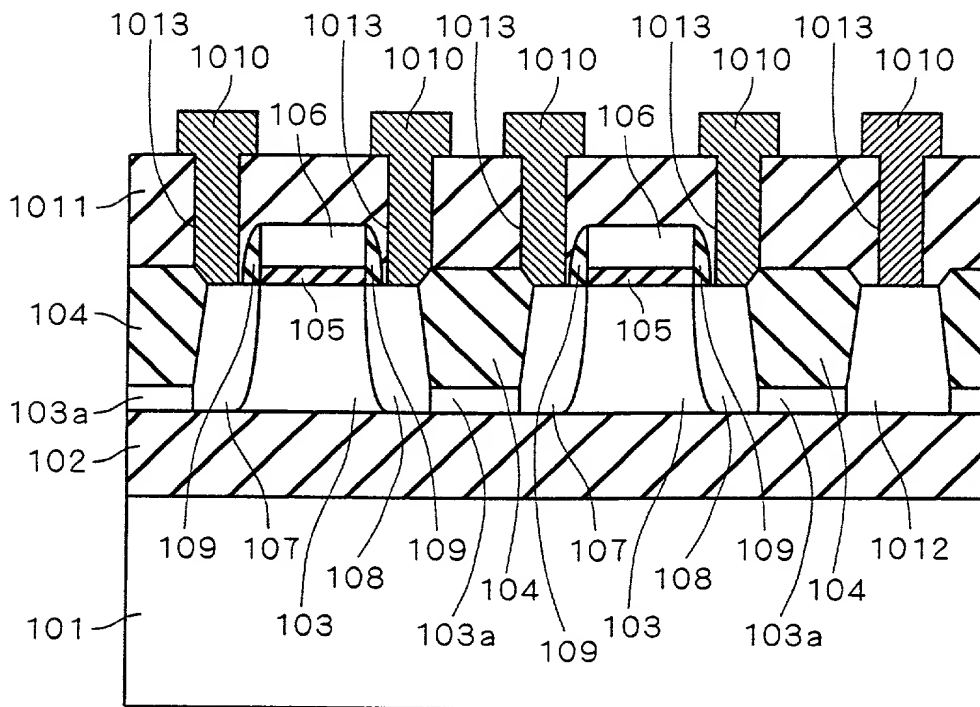
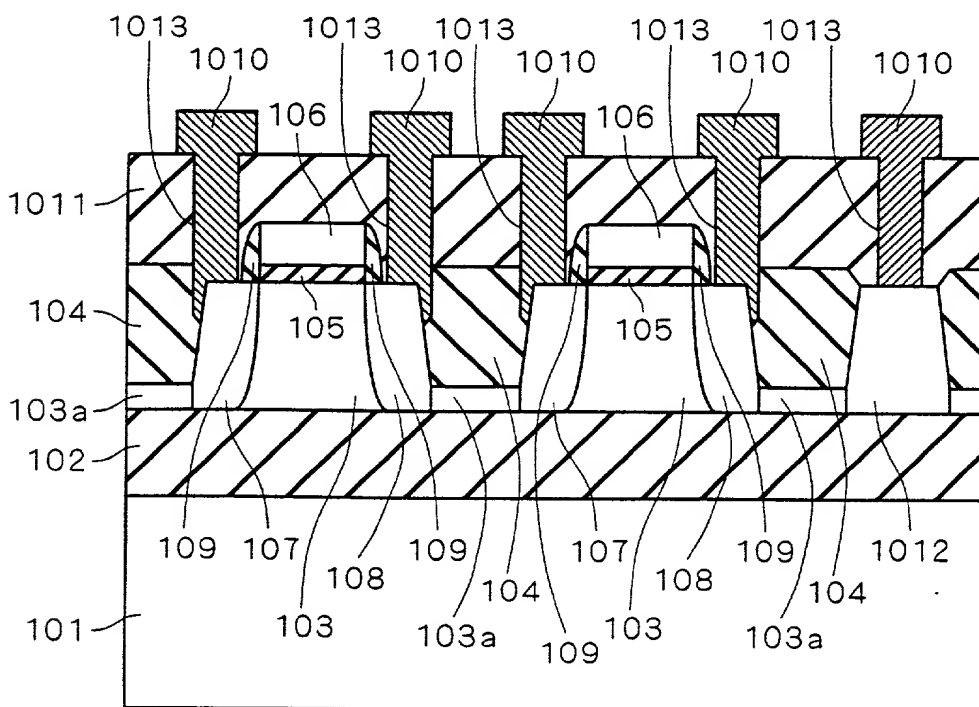


FIG. 24



200504US2 9:5027 9:5027 200504US2